

LCFI Detector Studies

Snowmass 2005, VTX WG

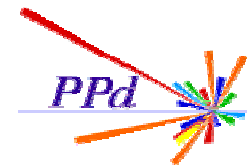
Joel Goldstein

CCLRC Rutherford Appleton Laboratory

For the LCFI Collaboration



Sensor Research



1. Column Parallel CCDs

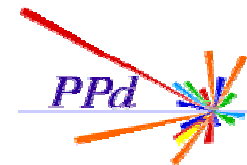
- Focus so far - building on past experience
- Readout during bunch train
- Clock drive major challenge

2. Storage Sensors

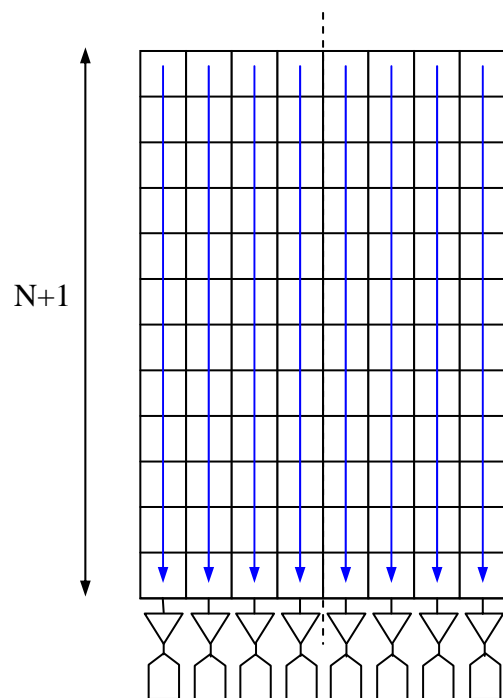
- Increased robustness
- Reduced driver requirements
- **ISIS** and **FAPS** technologies



Column Parallel CCD

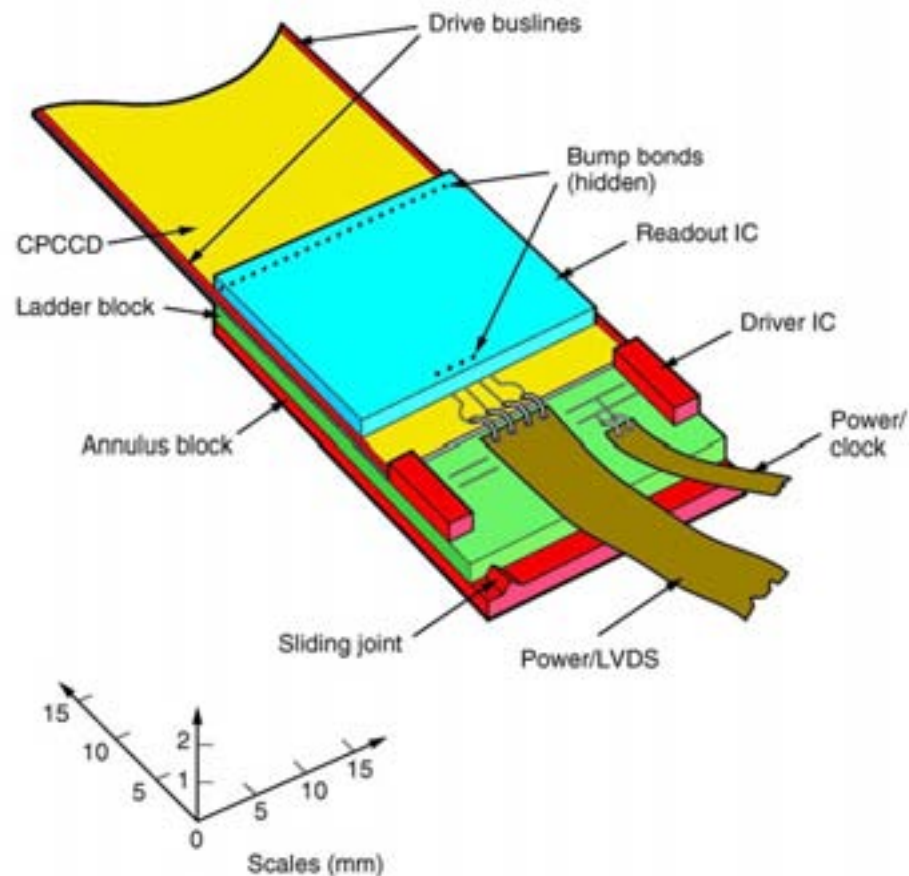


- Separate amplifier and readout for each column
- 50 MHz clock rate



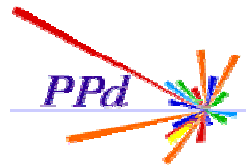
Column Parallel CCD

$$\text{Readout time} = (N+1)/F_{\text{out}}$$

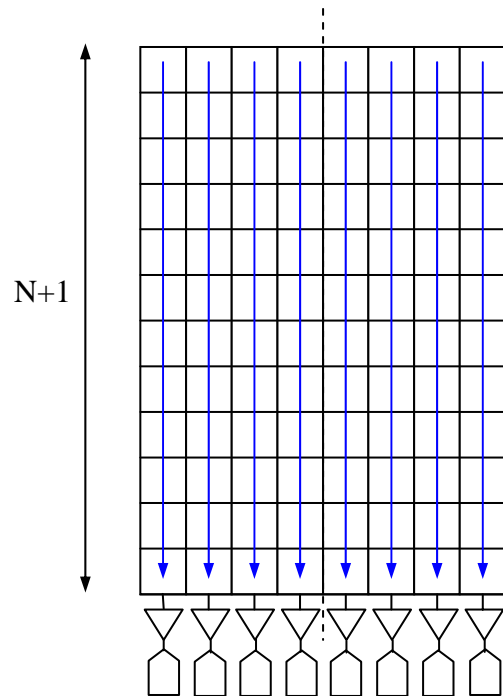




Column Parallel CCD

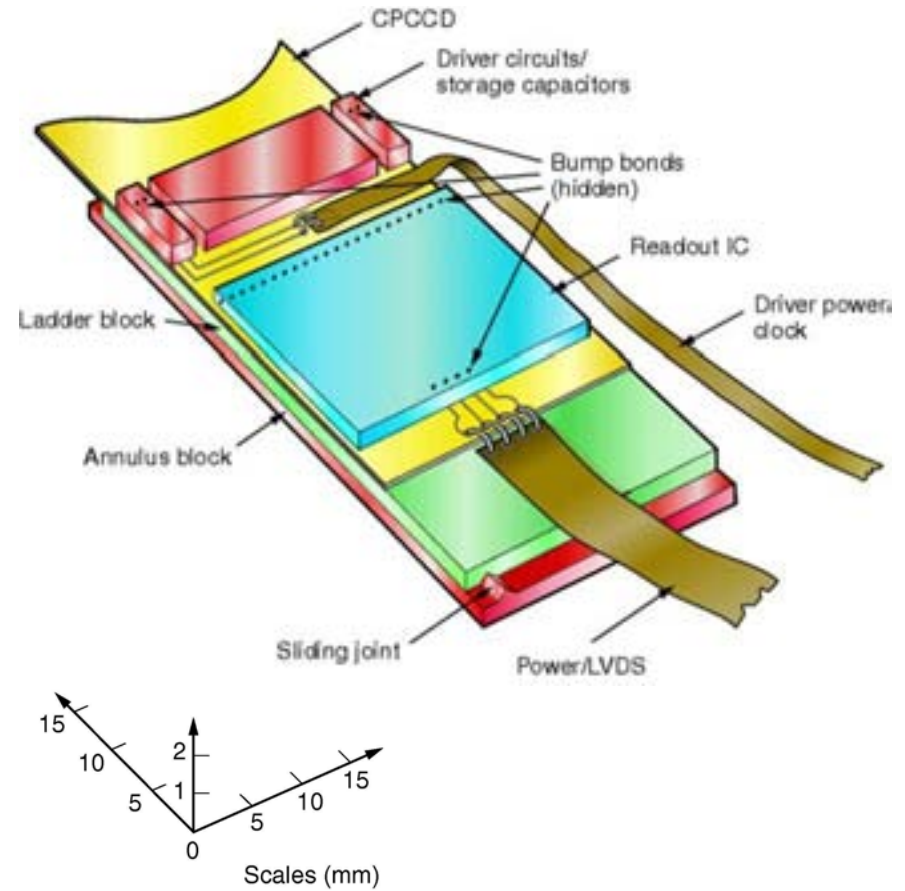


- Separate amplifier and readout for each column
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Column Parallel CCD

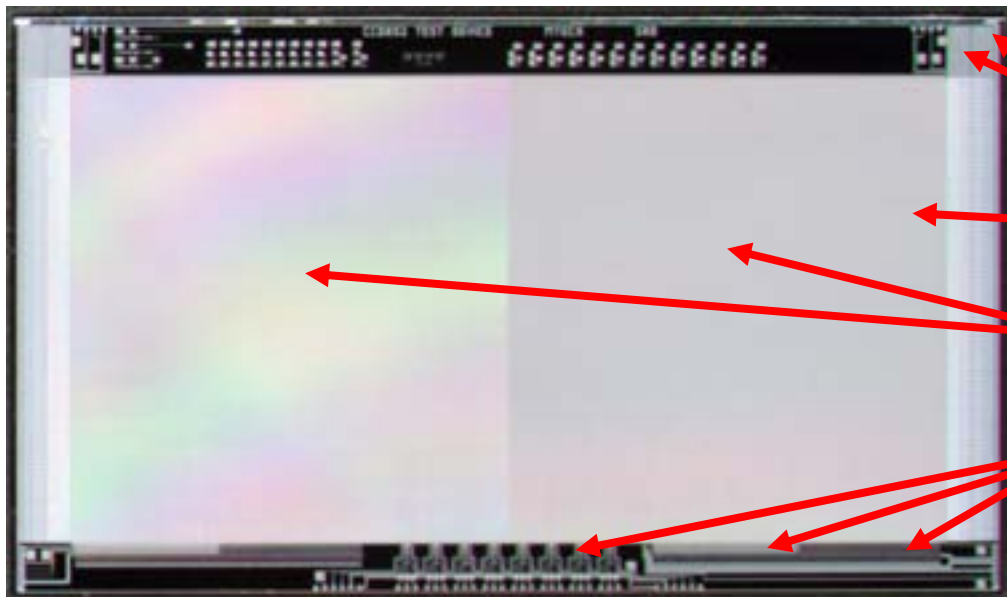
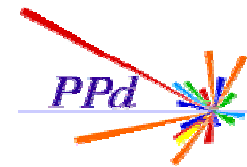
$$\text{Readout time} = (N+1)/F_{\text{out}}$$



- Clock drive is real challenge



Prototype CP CCD



CPC1 produced by E2V

- Two phase operation
- Metal strapping for clock
- 2 different gate shapes
- 3 different types of output
- 2 different implant levels

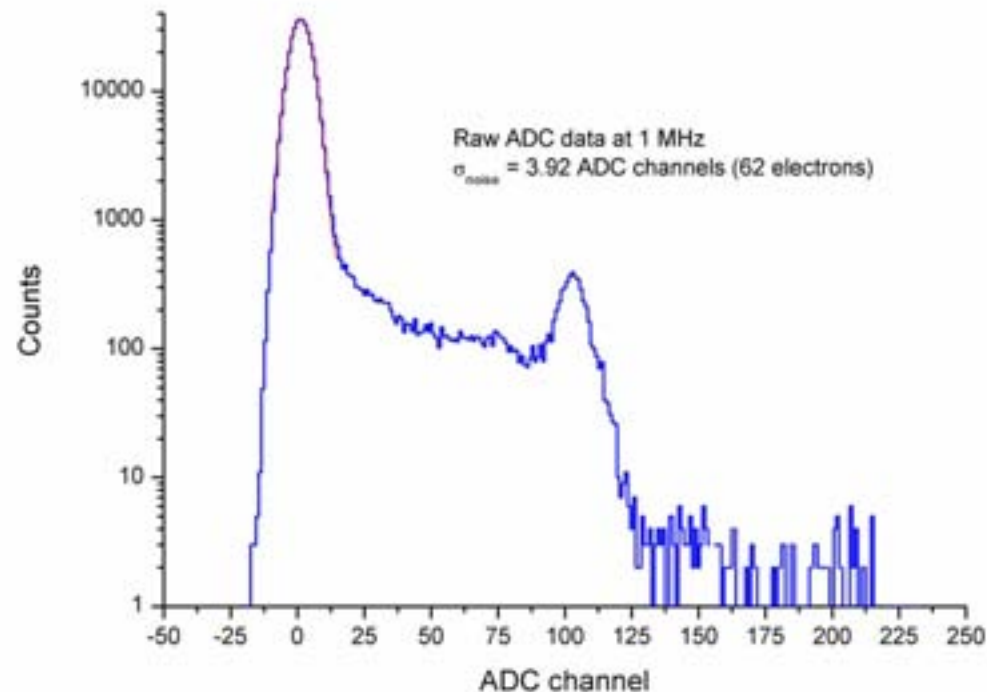
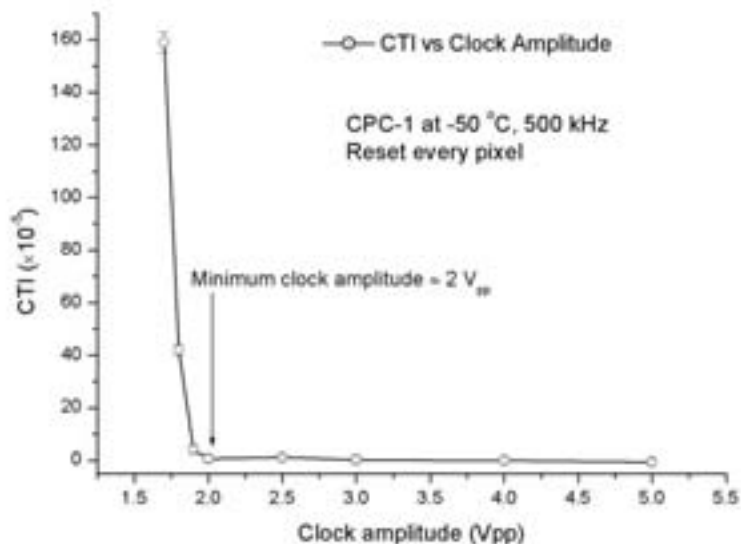
➤ *Clock with highest frequency at lowest voltage*



CPC1 Results



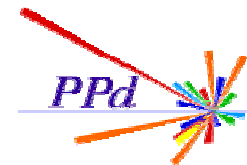
- Noise ~ 100 electrons
(60 after filter)
- Minimum clock ~1.9 V



- Maximum frequency > 25 MHz
– inherent clock asymmetry



CP Readout ASIC



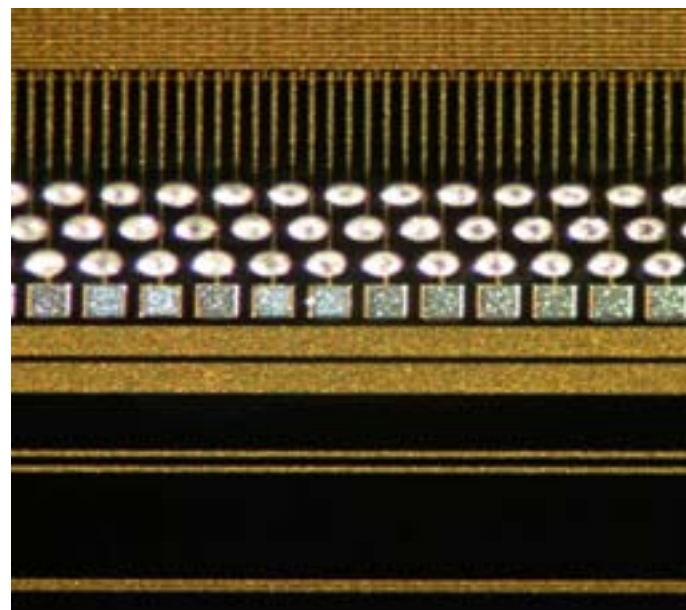
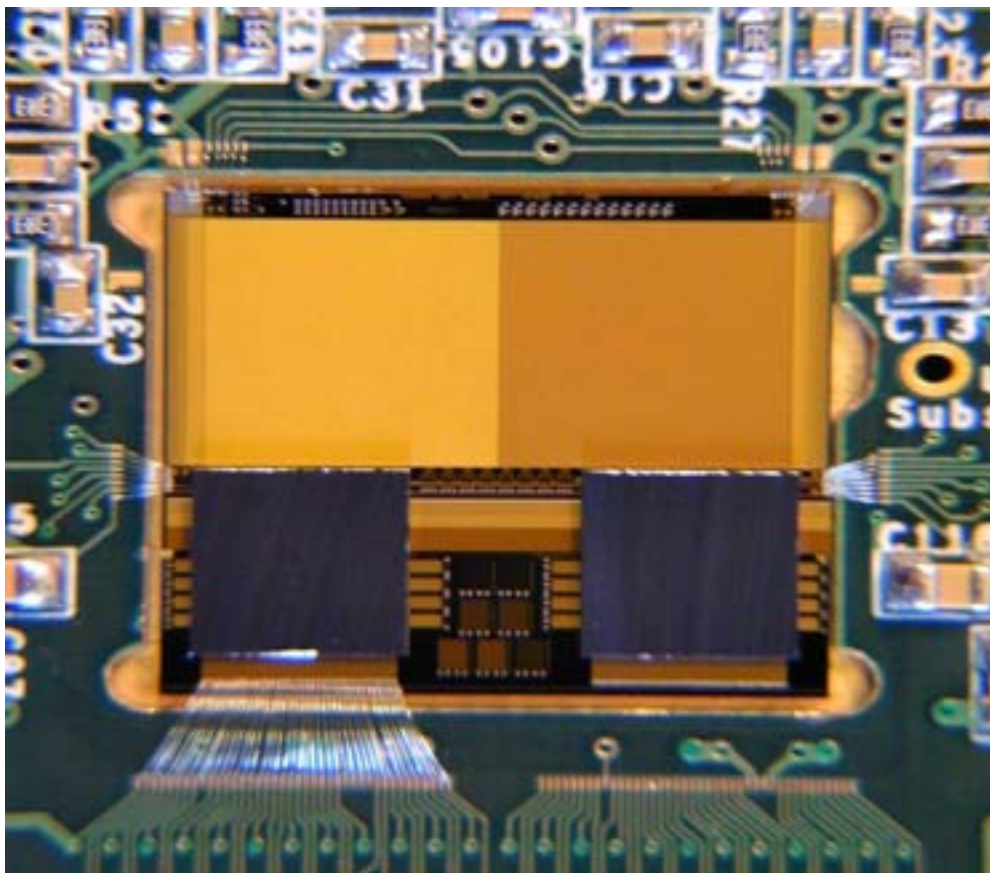
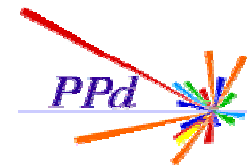
CPR1 designed by RAL ME Group

- IBM 0.25 μm process
- 250 parallel channels with 20 μm pitch
- Designed for 50 MHz
- Data multiplexed out through 2 pads





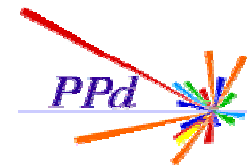
Bumped Assemblies



- Bonding by VTT, Finland
- Bump yield very high
- Some whole chip failures
 - *Not fully understood*

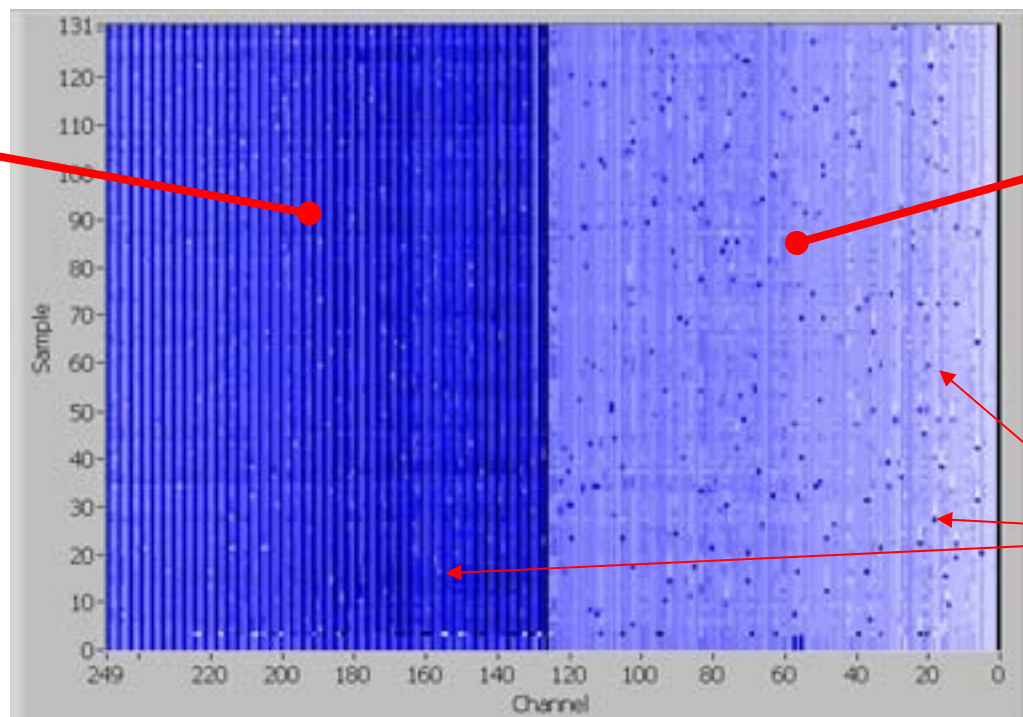


Testing Results



Charge Amplifiers
(inverting)

Voltage Amplifiers
(non-inverting)

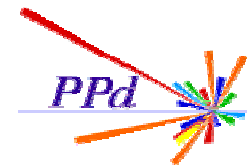


- Charge amplifiers work
- Negligible noise from CPR
- *Column parallel operation demonstrated*

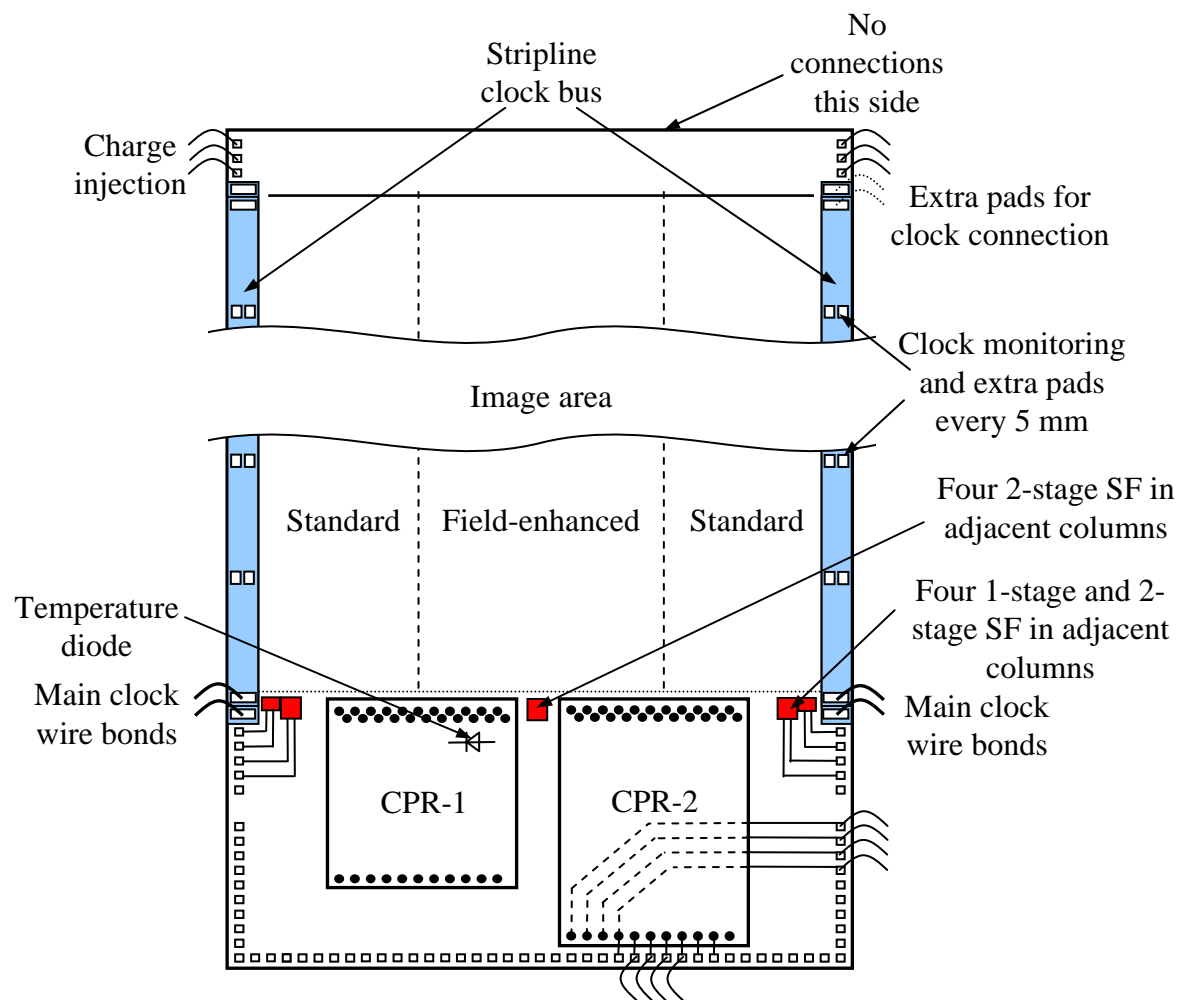
- No signal in ~20% of voltage channels
- Readout chip very sensitive to timing and bias issues
- Gain decrease towards centre of chip



Next Generation: CPC2

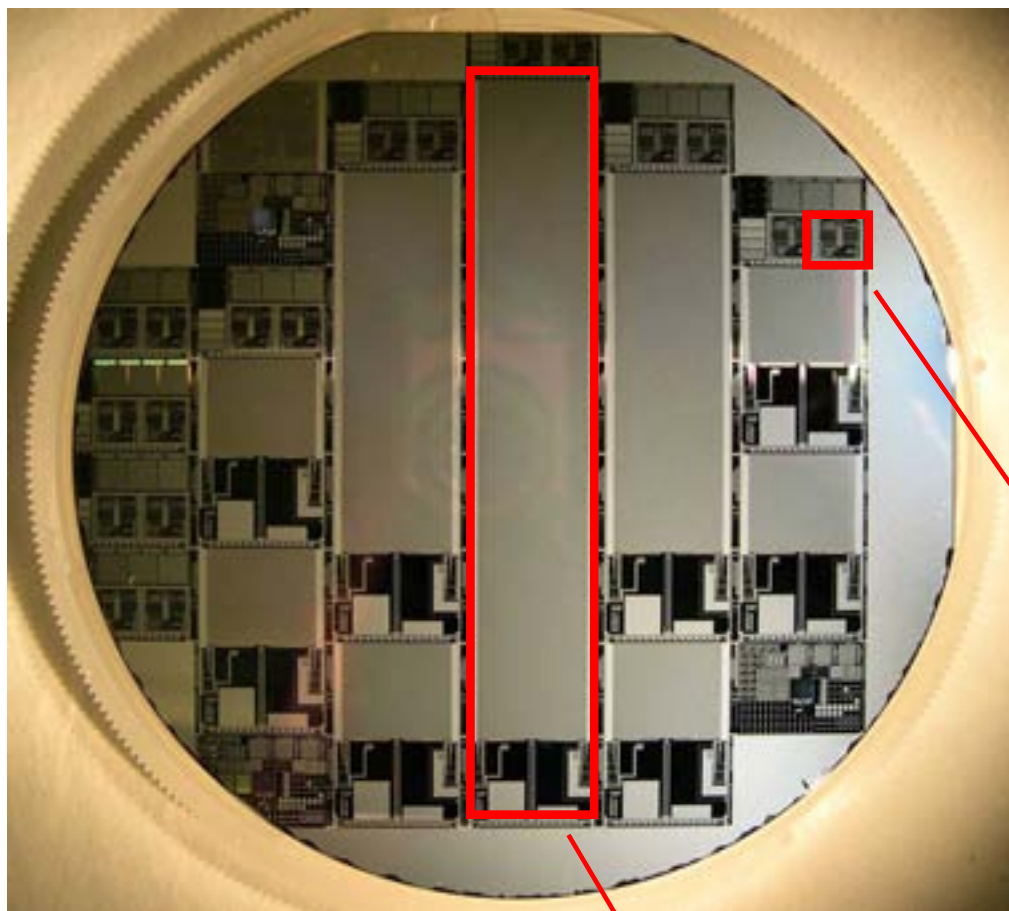
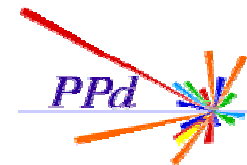


- Double metal now available from E2V
- Symmetric clock design
- “Busline-free” option
- Compatible with old and new readout chips

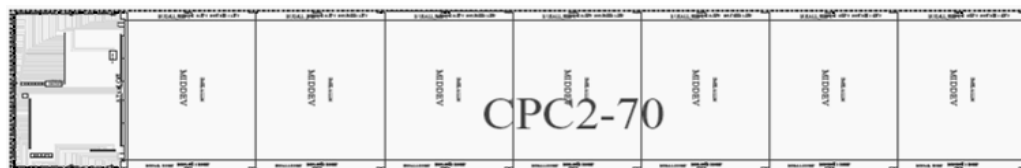
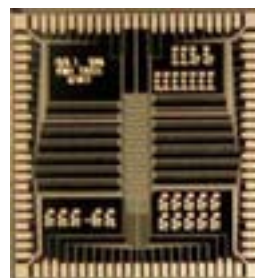




CPC2 Production

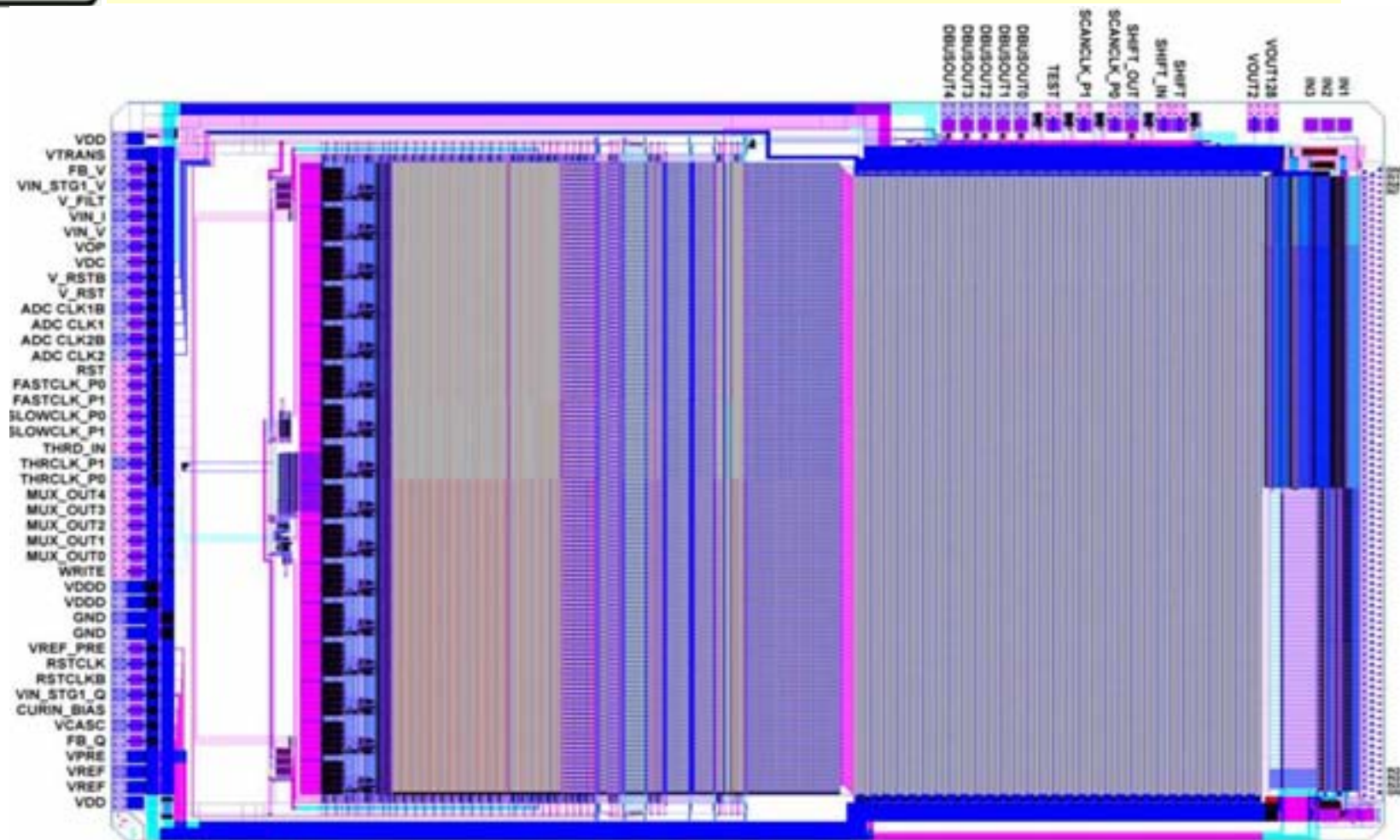
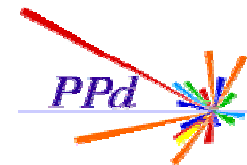


- Dedicated batch at e2v
- 3 sizes of CPCCD
 - *up to 92 mm active length*
- First wafers in DC probing
- Wafers include 16×16 ISIS





Next Generation: CPR2



Output

Sparsification
& Multiplexing

Cluster
Finding

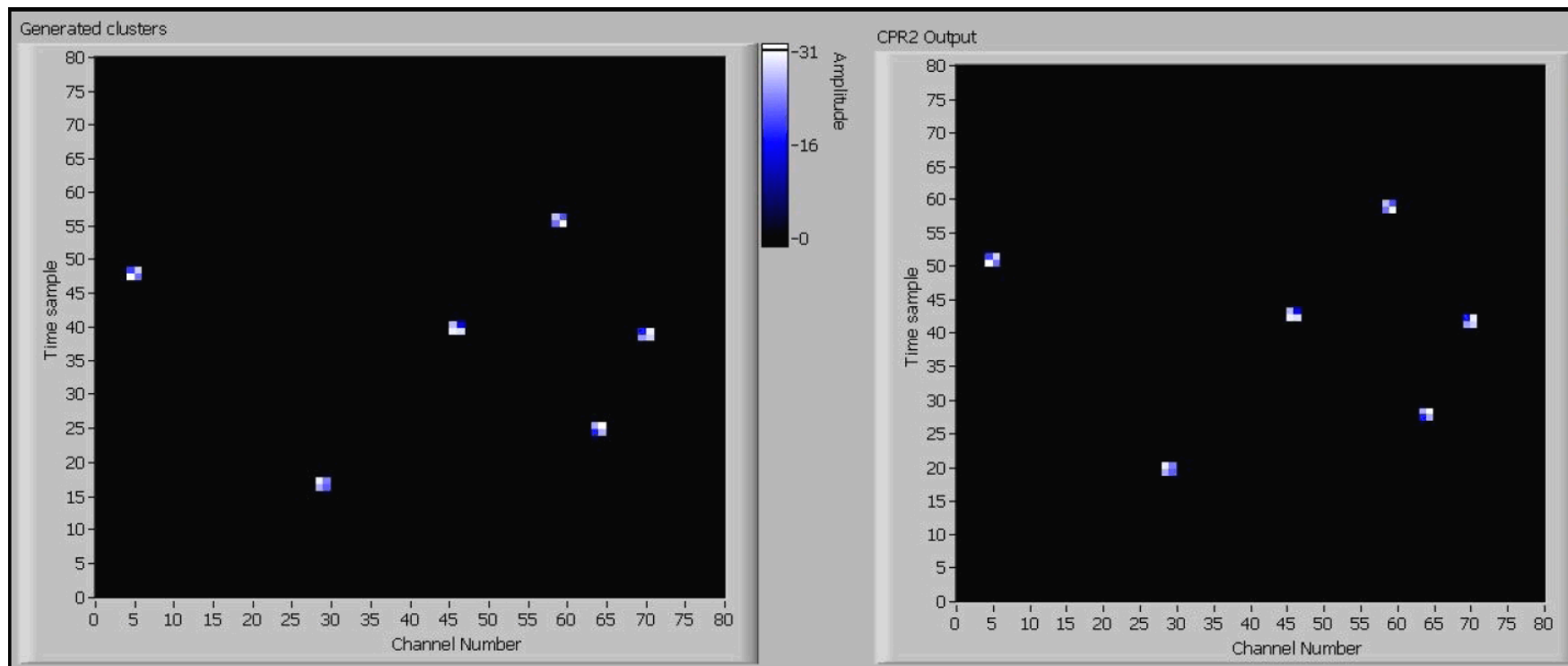
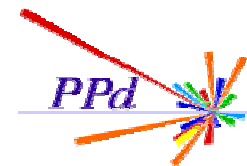
Binary
Conversion

5-bit ADC

Preamplifier Input



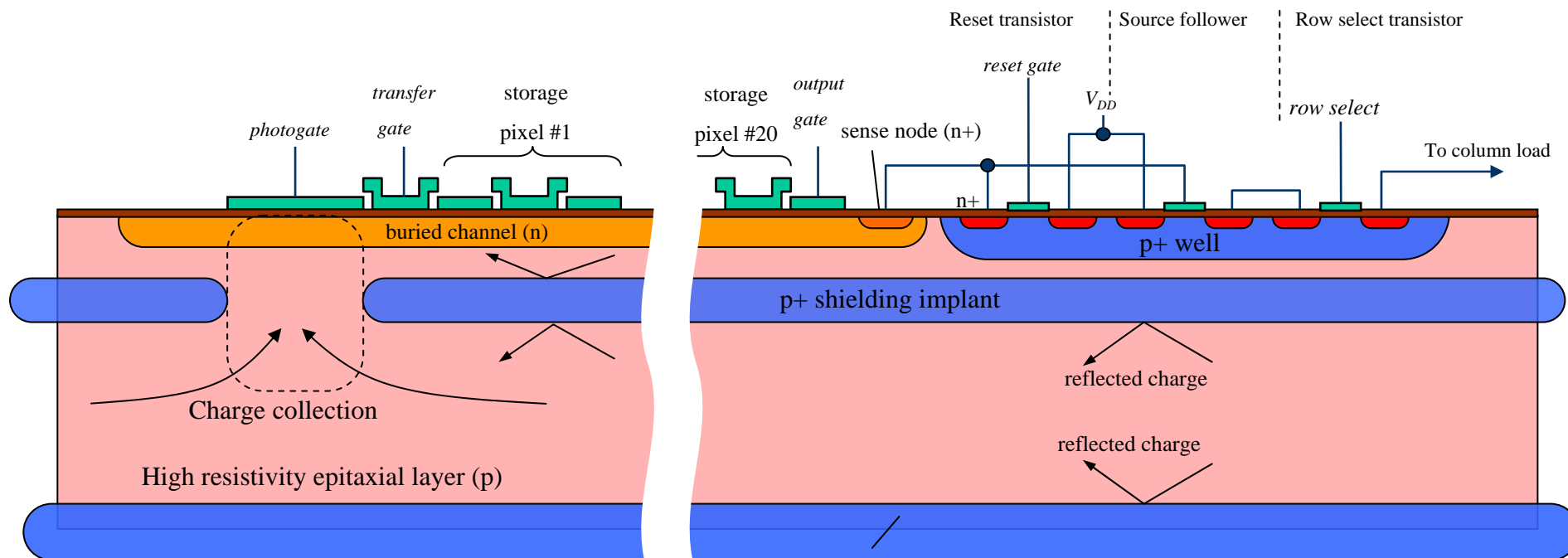
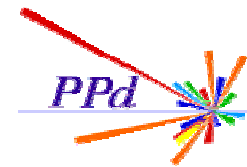
CPR2 Testing



- Cluster finding logic and sparse readout
- Improved amplifiers and ADCs
- Increased robustness



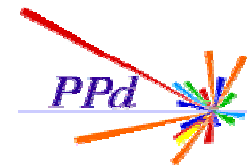
In-situ Storage Imaging Sensor



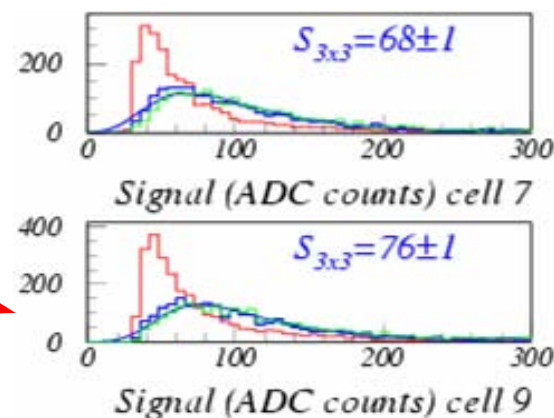
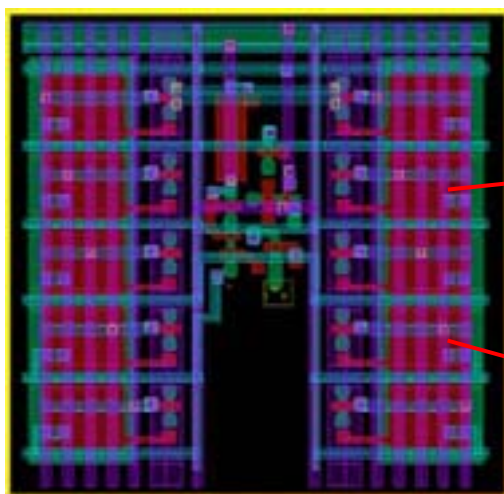
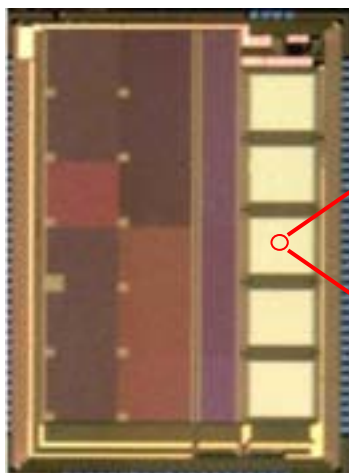
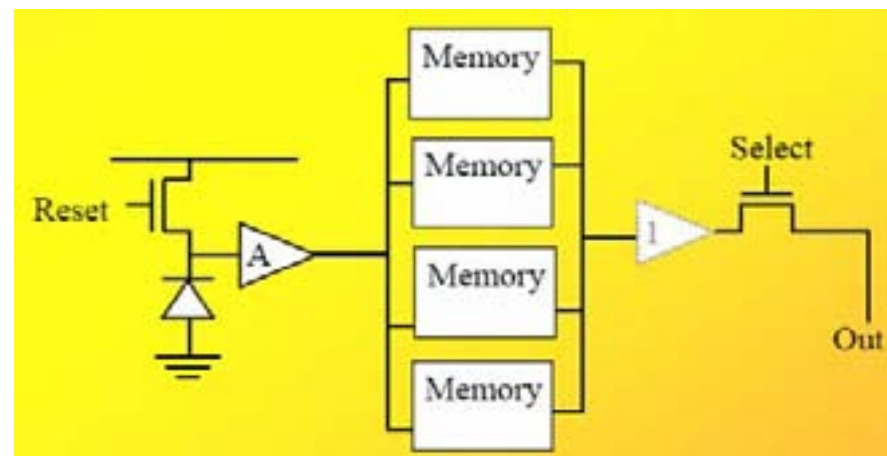
- Orders of magnitude increased resistance to RF
- Much reduced clocking requirements (*readout $\sim 1\text{MHz}$*)
- Combination of CCD and CMOS technology on small pitch



Flexible Active Pixel Sensors

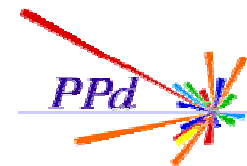


- **FAPS architecture**
 - First prototypes in 2004
 - Pixels $20 \times 20 \mu\text{m}^2$
 - 3 metal layers
 - 10 storage cells per pixel





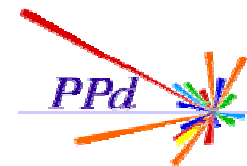
Plans



- **Test and evaluate 2nd generation CPCCD & readout**
- **Test first ISIS prototypes**
- **Design 3rd generation CPCCDs and drivers**
- **Develop ISIS and FAPS test structures**

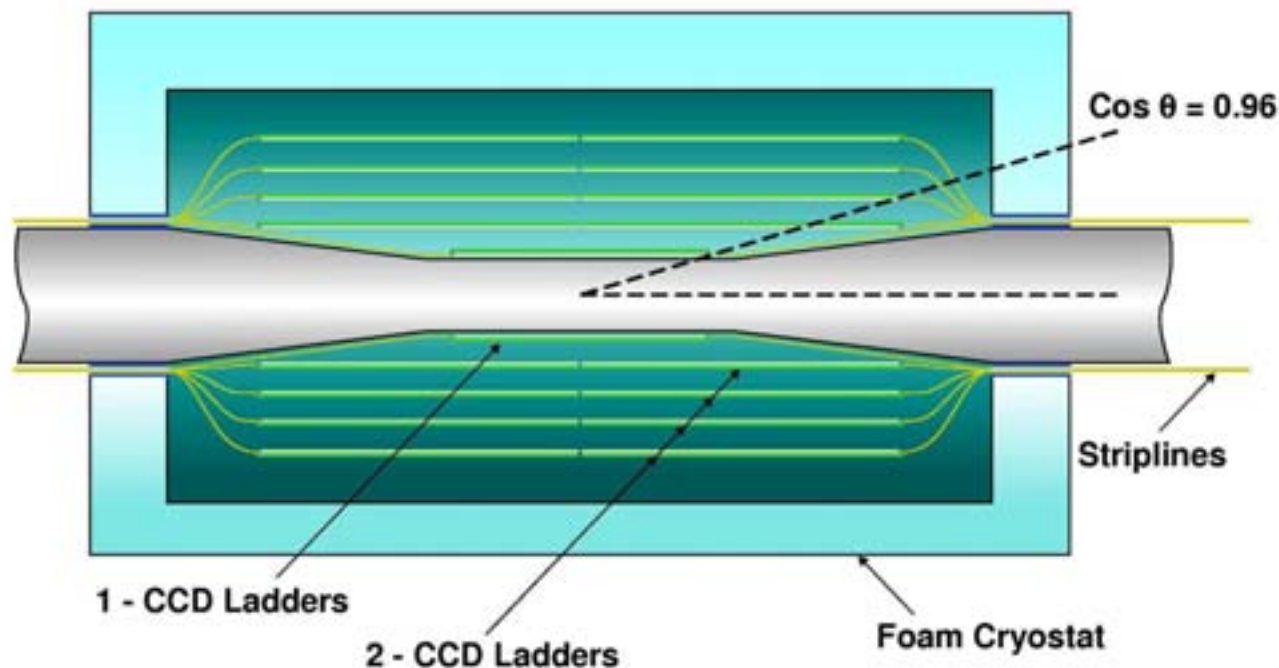
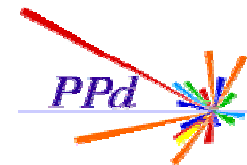


Backup Slides





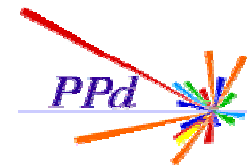
Baseline Vertex Detector



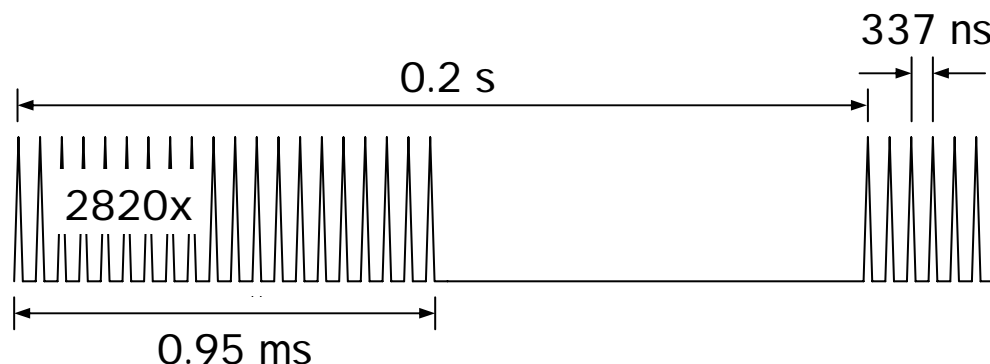
- 800 Mchannels of $20 \times 20 \mu\text{m}$ pixels in 5 layers
- Optimisation:
 - Inner radius (1.5 cm?)
 - Readout time ($50 \mu\text{s}$?)
 - Ladder thickness ($0.1\% X_0$?)



Sensors: The Challenge



Beam Time Structure:



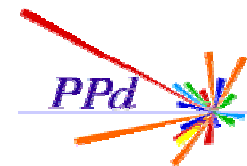
What readout speed is needed?

- Inner layer 1.6 MPixel sensors
 - Once per bunch = 300ns per frame : *too fast*
 - Once per train ~200 hits/mm² : *too slow*
 - 10 hits/mm² => 50μs per frame: **just right**
- (Fastest commercial imaging ~ 1 ms/MPixel)

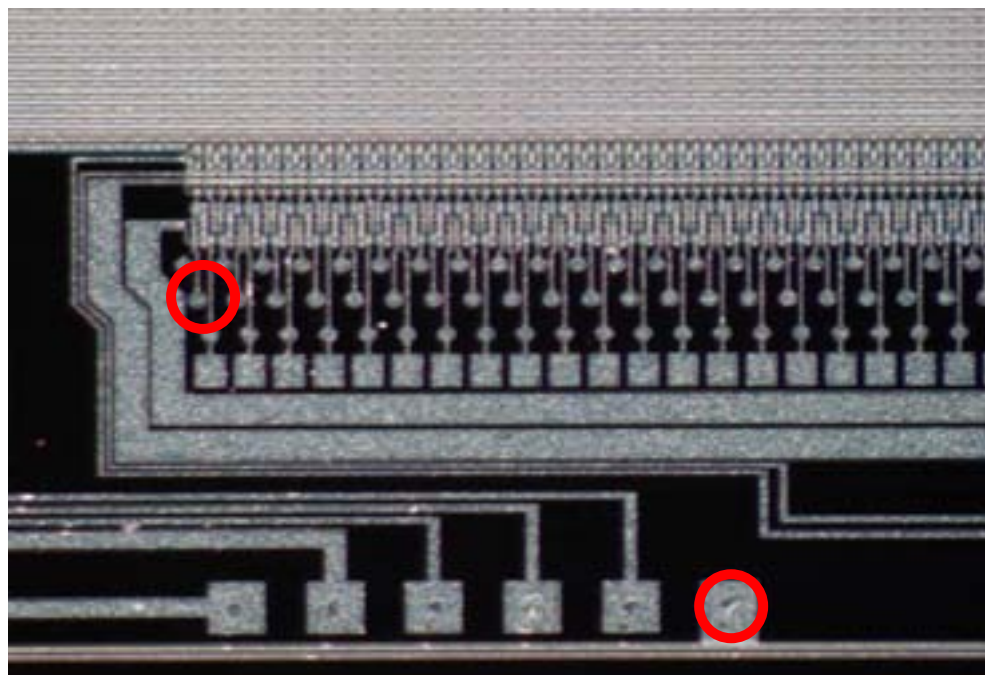
Power dissipation – gas volume cooling



Bumping Failures

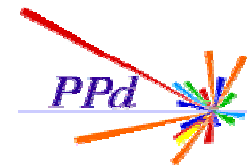


- Short between CCD substrate and chip ground
- Possible mechanical damage

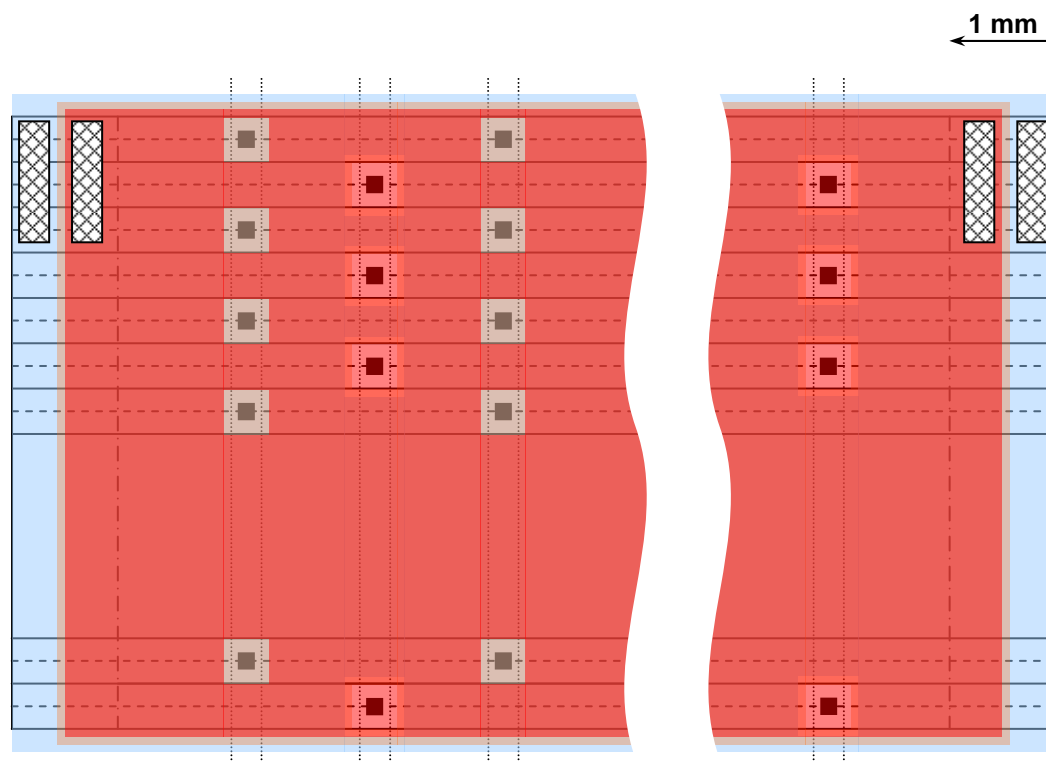




Busline Free CCDs



- Clock signals transmitted via distributed drive planes
 - Faster propagation
 - More uniform

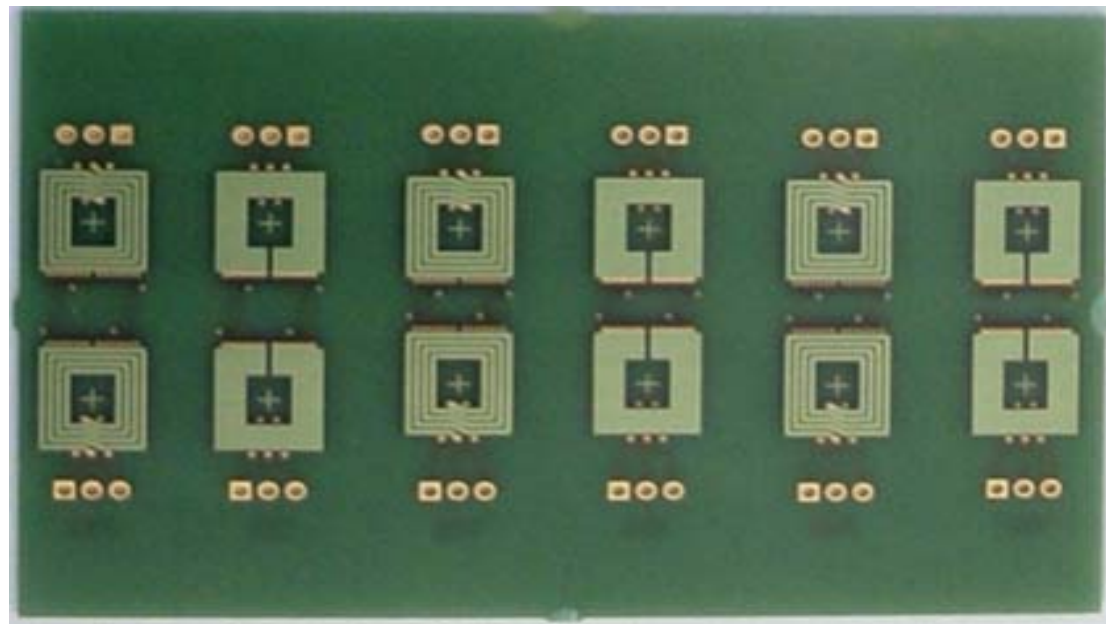


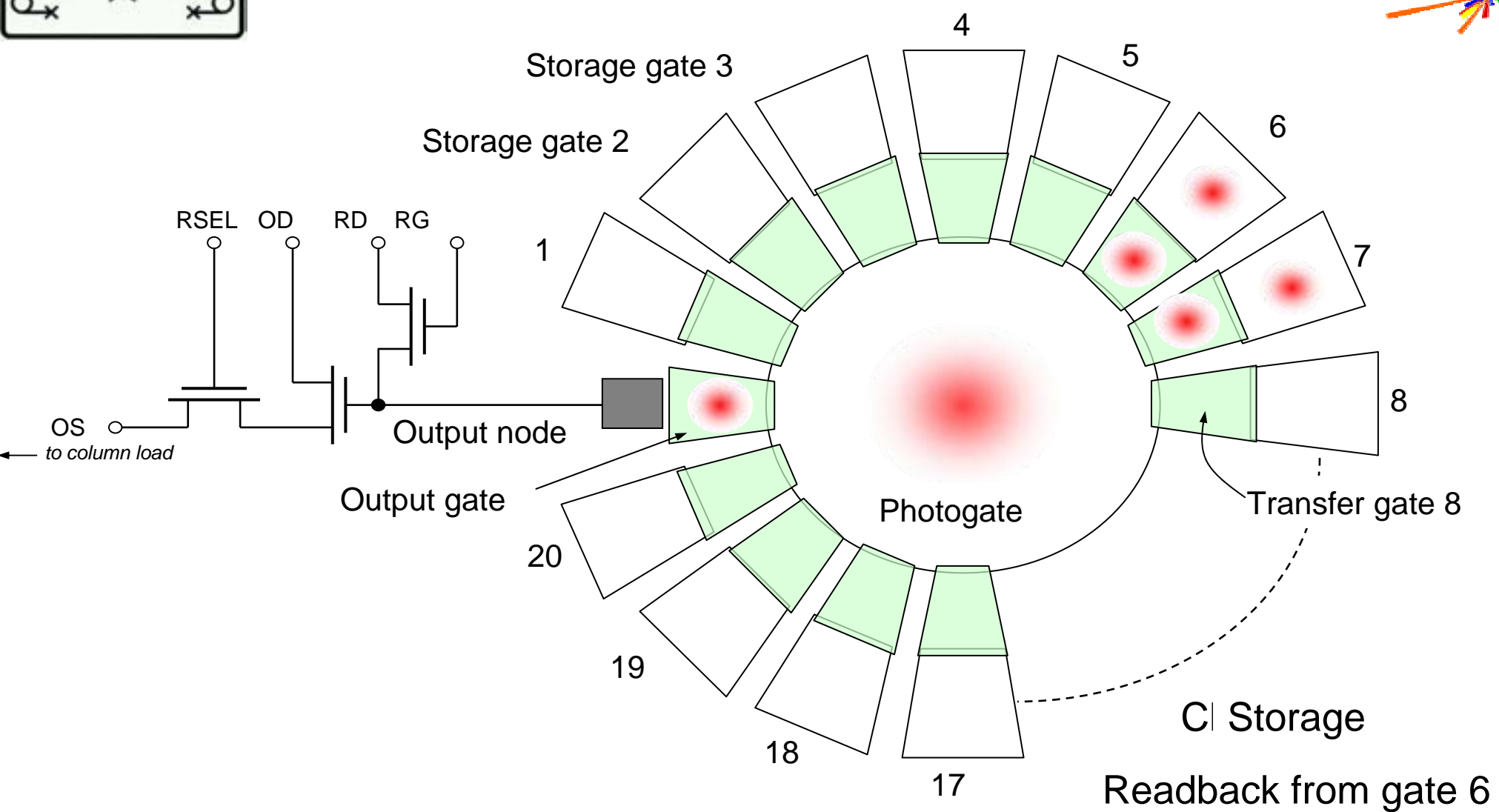
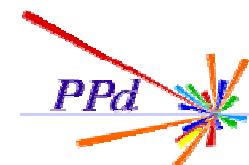


CCD Drivers



- **Clock drivers are a big challenge**
 - Working on air core PCB transformers
 - Long-term solution more likely to be IC with local storage

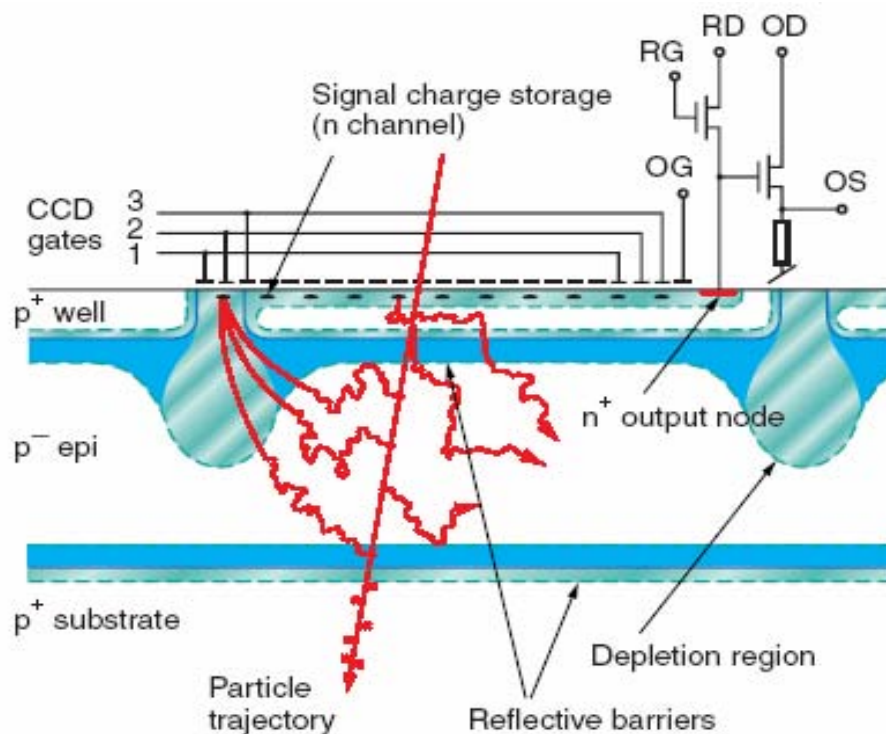
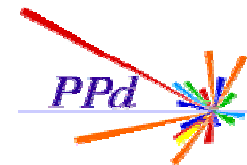




Idea by D. Burt and R. Bell (e2V)



In-situ Storage Imaging Sensors



1. Charge collection similar to CCD or CMOS
2. Charge transferred into local CCD array every 50 μ s
3. Local CCD array clocked at 20 kHz
4. Source follower for every pixel
5. Read out one row at a time
 - *Still column parallel*